

# March 2012 SuperFET<sup>®</sup> II

# FCP380N60 / FCPF380N60 600V N-Channel MOSFET

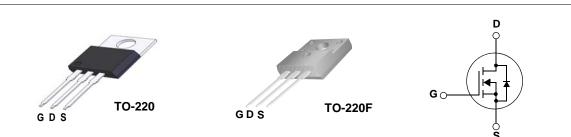
### Features

- 650V @T<sub>J</sub> = 150°C
- Max. R<sub>DS(on)</sub> = 380mΩ
- Ultra low gate charge (typ. Q<sub>g</sub> = 30nC)
- Low effective output capacitance (typ.  $C_{oss}$ .eff = 95pF)
- 100% avalanche tested

## Description

SuperFET<sup>®</sup>II is, Fairchild's proprietary, new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET<sup>®</sup>II is very suitable for various AC/DC power conversion in switching mode operation for system miniaturization and higher efficiency.



### Absolute Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter			FCP380N60	FCPF380N60	Units	
V <sub>DSS</sub>	Drain to Source Voltage			600		V	
M		-DC	-DC		±20		
V <sub>GSS</sub>	Gate to Source Voltage	-AC	(f>1HZ)	±30		V	
1		-Continuous (T <sub>C</sub> = 25°C)		10.2	10.2*	•	
I <sub>D</sub>	Drain Current	-Continuous ( $T_C = 100^{\circ}C$ )		6.4	6.4*	A	
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)		30.6	30.6*	А	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Not		(Note 2)	211.6		mJ	
I <sub>AR</sub>	Avalanche Current		(Note 1)	2.3		А	
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	) 1.06		mJ	
dv/dt	Peak Diode Recovery dv/dt (No		(Note 3)	3) 20		V/ns	
uv/ui	MOSFET dv/dt			100		v/ns	
P <sub>D</sub>	Devues Dissischier	$(T_{C} = 25^{\circ}C)$		106	31	W	
	Power Dissipation	- Derate above 25°C		0.85	0.25	W/ºC	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150		°C		
TL	Maximum Lead Temperature for Soldering Purpose,         300           1/8" from Case for 5 Seconds         300			00	°C		

\*Drain current limited by maximum junction temperature

### **Thermal Characteristics**

Symbol	Parameter	FCP380N60	FCPF380N60	Units
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	1.18	4	
$R_{\theta CS}$	Thermal Resistance, Case to Heat Sink (Typical)	0.5	0.5	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient	62.5	62.5	

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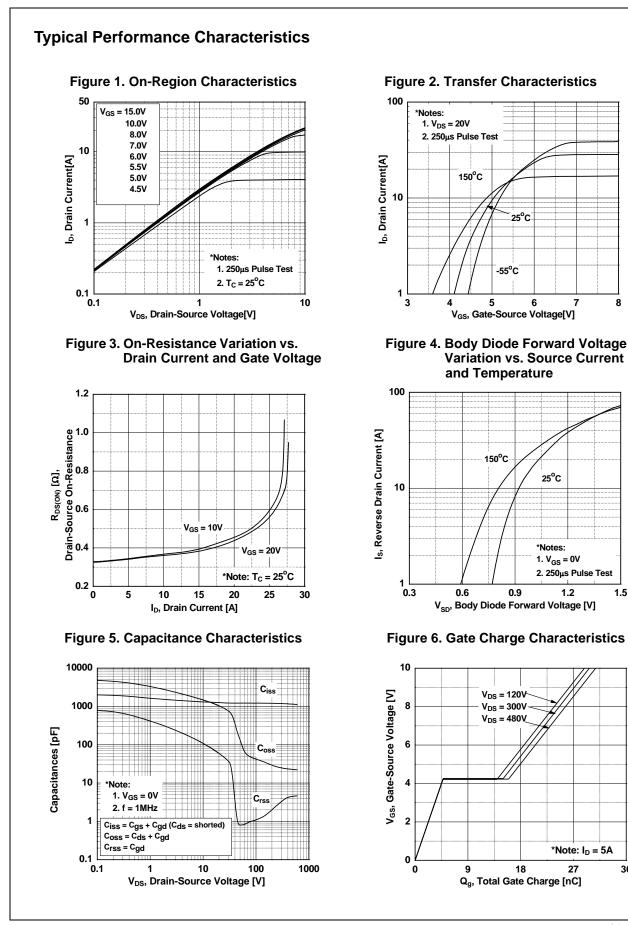
Device Marking		Device	Packag	e	Reel Size	Тар	e Width		Quantit	у
		TO-220	2	-		-		50		
FCPF380	N60	FCPF380N60	TO-220	F	-		-		50	
Electrica	I Char	acteristics T <sub>c</sub> =	25ºC unless	otherwis	e noted					
Symbol		Parameter			Test Conditions		Min.	Тур.	Max.	Unit
Off Charac	teristic	S								
		<b>2 2 1 1 1</b>		V <sub>GS</sub> = 0V, I <sub>D</sub> = 10mA, T <sub>J</sub> = 25°C		600	-	-	V	
BV <sub>DSS</sub>	Drain to	Source Breakdown Vo	oltage		$V, I_D = 10 \text{mA}, T_J = 1$		650	-	-	V
ΔBV <sub>DSS</sub> ΔTJ	Breakdo	own Voltage Temperatu ent	ıre	$I_D = 10$ mA, Referenced to 25°C		-	0.6	-	V/ºC	
BV <sub>DS</sub>		ource Avalanche Brea	kdown	$V_{GS} = 0$	0V, I <sub>D</sub> = 10A		-	700	-	V
Voltage				$V_{De} = 4$	480V, V <sub>GS</sub> = 0V		-	-	1	
I <sub>DSS</sub>	Zero Ga	ate Voltage Drain Curre	ent	-	480V, T <sub>C</sub> = 125°C		-	-	10	μA
I <sub>GSS</sub>	Gate to	o Body Leakage Current			$\pm 20V, V_{DS} = 0V$		-	-	±100	nA
	Į			00	50	ļ	ļ		Į	1
On Charac				N/	V 1 050 A		0.5		25	V
V <sub>GS(th)</sub>		e Threshold Voltage		$V_{GS} = V_{DS}, I_D = 250 \mu A$		2.5	-	3.5	V	
R <sub>DS(on)</sub>		Drain to Source On Resistance		$V_{GS} = 10V, I_D = 5A$ $V_{DS} = 20V, I_D = 5A$		-	0.33	0.38	Ω S	
9fs				vDS =						0
Dynamic C	haracte	eristics								
C <sub>iss</sub>	Input Ca	apacitance				-	1250	1665	pF	
C <sub>oss</sub>	Output (	t Capacitance se Transfer Capacitance		$- V_{\text{DS}} = 25V, V_{\text{GS}} = 0V$ - f = 1MHz		-	905	1205	pF	
C <sub>rss</sub>	Reverse					-	45	60	pF	
C <sub>oss</sub>	Output 0	Capacitance		$V_{DS} = 380V, V_{GS} = 0V, f = 1.0MHz$		-	23	-	pF	
C <sub>oss</sub> eff.	Effective	ve Output Capacitance		$V_{DS} = 0V \text{ to } 480V, V_{GS} = 0V$ $V_{DS} = 380V, I_D = 5A$ $V_{GS} = 10V$ (Note 4)		-	95	-	pF	
Q <sub>g(tot)</sub>	Total Ga	Gate Charge at 10V o Source Gate Charge o Drain "Miller" Charge				-	30	40	nC	
Q <sub>gs</sub>	Gate to					-	5	-	nC	
Q <sub>gd</sub>						-	10	-	nC	
ESR	Equivale	ent Series Resistance		Drain Open			1		Ω	
Switching	Charac	teristics								
t <sub>d(on)</sub>	Turn-On	Delay Time				-	14	38	ns	
t <sub>r</sub>	Turn-On	-On Rise Time -Off Delay Time		$V_{DD} = 380V, I_D = 5A$ $V_{GS} = 10V, R = 4.7\Omega$ (Note 4)		-	7	24	ns	
t <sub>d(off)</sub>	Turn-Off					-	45	100	ns	
t <sub>f</sub>	Turn-Off	rn-Off Fall Time				-	6	22	ns	
Drain-Sou	ce Dior	de Characteristic	e							
I <sub>s</sub>	1			e Forwar	d Current		-	-	10.2	A
I <sub>SM</sub>		Maximum Continuous Drain to Source Diod Maximum Pulsed Drain to Source Diode Fo				-	-	30.6	A	
V <sub>SD</sub>		ain to Source Diode Forward Voltage		$V_{GS} = 0V, I_{SD} = 5A$		-	-	1.2	V	
t <sub>rr</sub>		Recovery Time	30		$V, I_{SD} = 5A$		-	240	-	ns
Q <sub>rr</sub>					= 100A/μs	F	-	2.7	-	μC
<b>A</b> ll	11010100	erse Recovery Charge					2		μΟ	

 $\begin{array}{l} 3. \ I_{SD} \leq 5.1 A, \ di/dt \leq 200 A/\mu s, \ V_{DD} \leq B V_{DSS}, \ Starting \ T_J = 25^\circ C \\ 4. \ Essentially Independent of Operating Temperature Typical Characteristics \end{array}$ 

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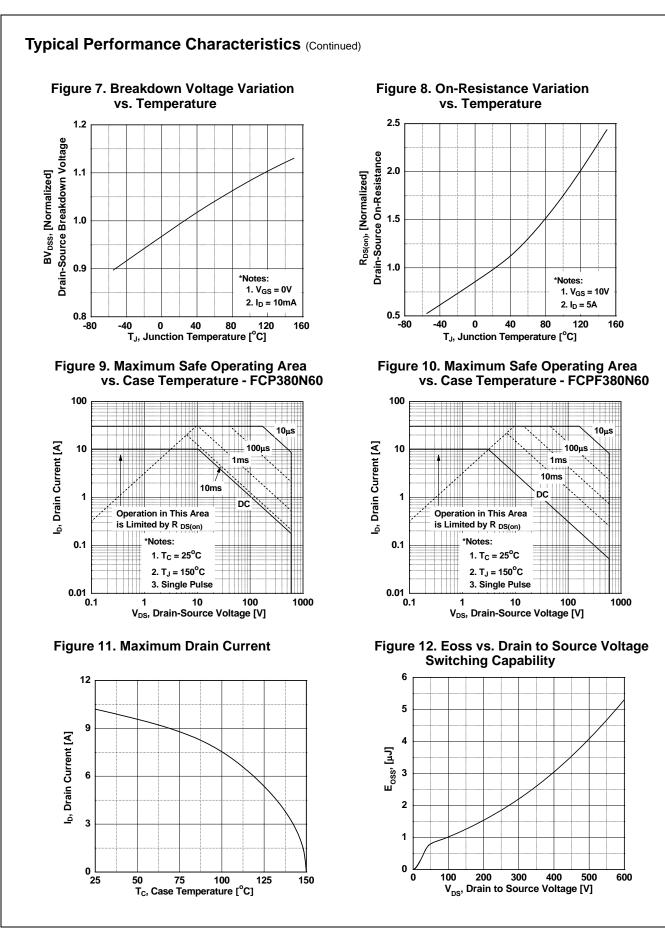
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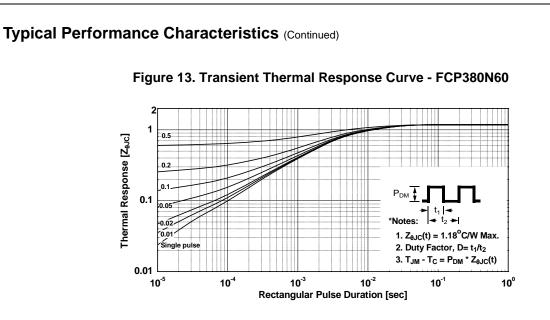
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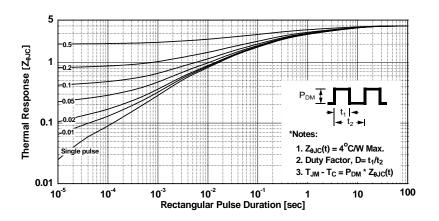
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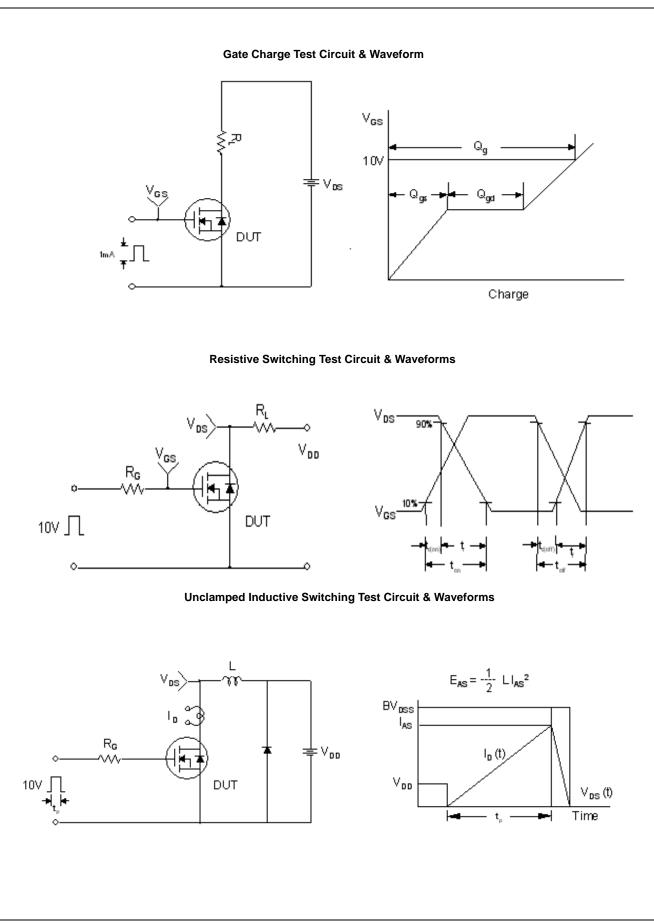






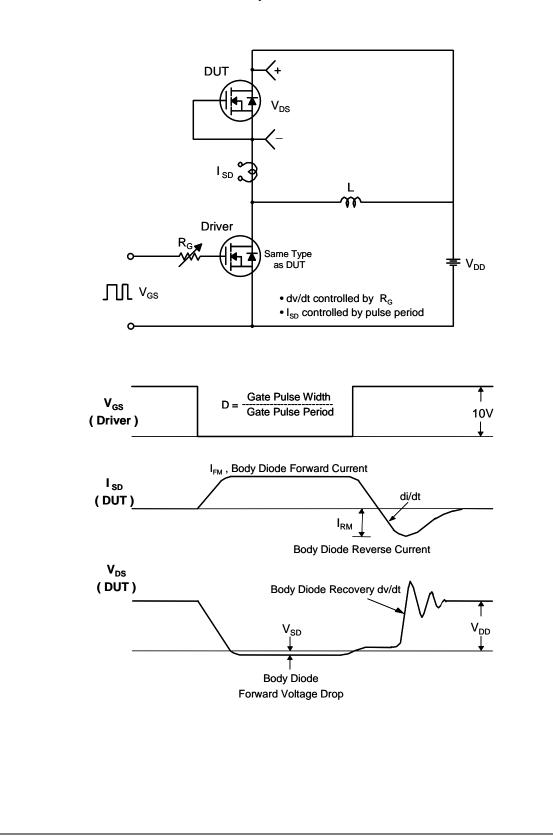


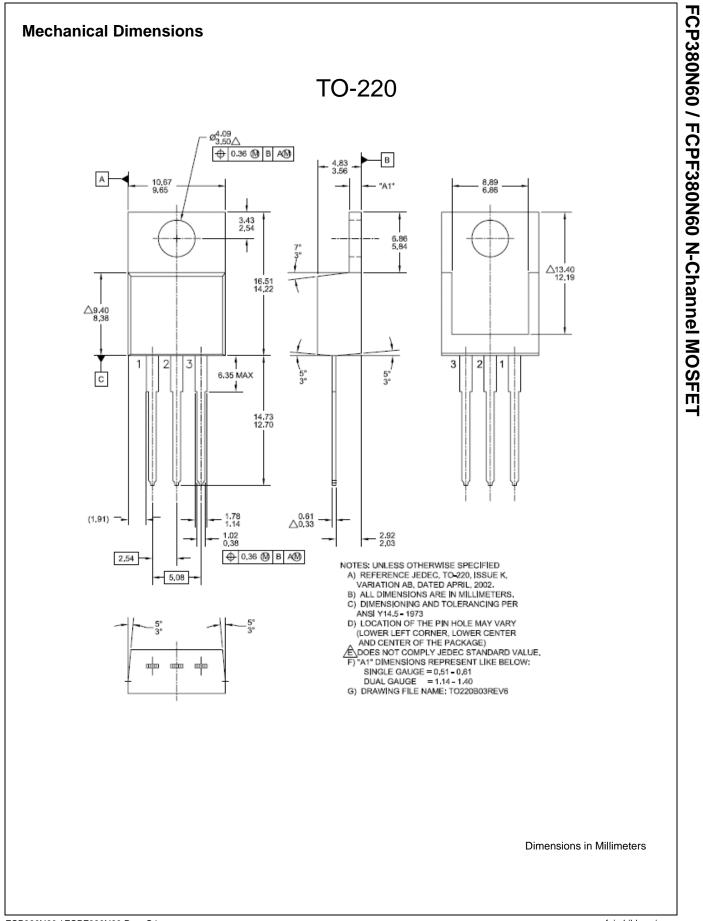


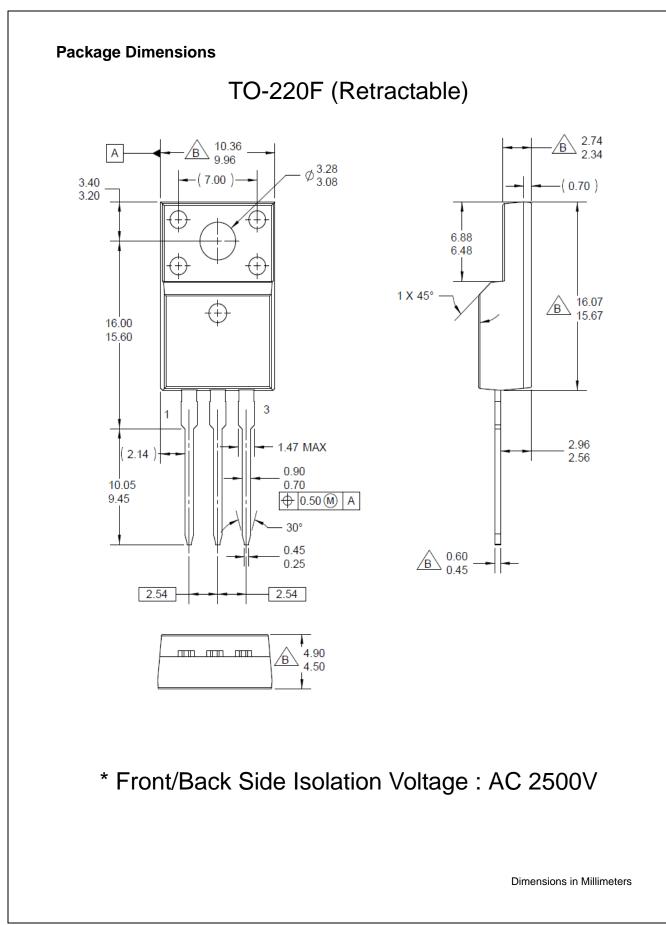


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### Peak Diode Recovery dv/dt Test Circuit & Waveforms









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